

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED
CENTRAL FAX CENTER

MAY 25 2004

OFFICIAL

Serial No.: 10/647,714

Conf. No.: 2476

Filing Date: 08/25/2003

Art Unit: 2818

Applicant: Khan et al.

Examiner: Le, Thao P.

Title: METAL OXIDE SEMICONDUCTOR
HETEROSTRUCTURE FIELD EFFECT
TRANSISTOR

Docket No.: SETI-0002DIV

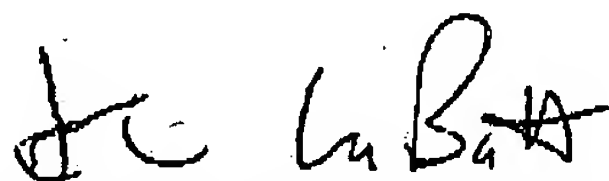
COMMISSIONER FOR PATENTS

DESTINATION PHONE NUMBER: 703-872-9306

Transmitted herewith is: Amendment in 11 pages

in the above identified application.

- ☒ No additional fee is required.
- ☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 500999 as described below.
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.



John W. LaBatt, Reg. No. 48,301

DATE: May 25, 2004

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office on the date shown below.

John LaBatt
(Person transmitting this correspondence)
Signature5/25/04
Date

If you receive this correspondence in error or do not receive the entire transmission, please notify us at (518) 449-0044.

RECEIVED
CENTRAL FAX CENTER
MAY 25 2004
OFFICIAL

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/647,714

Conf. No.: 2476

Filing Date: 08/25/2003

Art Unit: 2818

Applicant: Khan et al.

Examiner: Le, Thao P.

Title: METAL OXIDE SEMICONDUCTOR
HETEROSTRUCTURE FIELD EFFECT
TRANSISTOR

Docket No.: SETI-0002DIV

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

This paper is being filed in response to the Office Action dated March 11, 2004. Please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims that begins on page 2 of this paper.

Remarks begin on page 7 of this paper.

Serial No. 10/647,714

Page 1 of 11